

Amendments to the Claims:

This listing of claims will replace all prior listings of claims in the application.

Listing Of Claims:

1 (CURRENTLY AMENDED): A mask comprising plural contact hole patterns ~~that form a line, and plural auxiliary patterns, each having an area~~ auxiliary pattern being smaller than that of each contact hole pattern,

wherein the plural auxiliary patterns include a first auxiliary pattern and ~~[[a]] plural second auxiliary pattern patterns, centers of the contact hole patterns and a center of the first auxiliary pattern having an opening having a center that is aligned with the line, the first auxiliary pattern being located apart from a contact hole pattern at an end of the plural contact hole patterns by a period of the plural contact hole patterns being at regular periods in a line, the plural second auxiliary pattern patterns each~~ having an opening having a center that is offset from the line and equally distant from two adjacent centers among the contact hole patterns and the first auxiliary pattern, and the second auxiliary pattern being equally distant from both the first auxiliary pattern and the contact hole pattern at the end

wherein the plural second auxiliary patterns are arranged at both sides of the line.

2-13 (CANCELLED):

14 (CURRENTLY AMENDED): An exposure method comprising the step of illuminating a mask according to claim 1 by using ~~[[a]]~~ light that enables the plural contact hole patterns to resolve and prevents the plural auxiliary patterns from resolving, and exposing an object using the light from the mask.

15-16 (CANCELLED):

17 (CURRENTLY AMENDED): An exposure method according to claim 14, wherein the light that enables the plural contact hole patterns to resolve and prevents the plural auxiliary patterns from resolving form an effective light source ~~[[has]]~~ having a dark center portion.

18-19 (CANCELLED):

20 (CURRENTLY AMENDED): A mask designing method for designing a mask that includes plural contact hole patterns ~~that form a line~~, and plural auxiliary patterns having a first auxiliary pattern and plural second auxiliary patterns, each ~~having an area~~ auxiliary pattern being smaller than that of each contact hole pattern, the mask enabling plural contact hole patterns to resolve and while preventing the plural auxiliary ~~pattern patterns~~ from resolving, said mask designing method comprising the steps of:

arranging a first auxiliary pattern ~~having an opening that has a center that is aligned with the line, the first auxiliary pattern being located apart from a contact hole pattern at an end of the plural contact hole patterns by a period of the plural contact hole patterns so that centers of the contact hole patterns and a center of the first auxiliary pattern being at regular periods in a line~~; and ~~[[.]]~~

arranging ~~[[a]]~~ plural second auxiliary pattern ~~patterns~~ each having an opening ~~having a center that is offset from the line, and the second auxiliary pattern being~~ equally distant from both two adjacent centers among the first auxiliary pattern and the contact hole pattern ~~at the end patterns~~, and the plural auxiliary patterns ~~including the first and second auxiliary patterns~~ the plural second auxiliary patterns are located at both sides of the line.

21 (CANCELLED):

22 (PREVIOUSLY PRESENTED): A device fabricating method comprising the steps of:
exposing an object by using an exposure method according to claim 14; and developing the
object that has been exposed.

23 (NEW): A mask according to claim 1, wherein centers of the plural auxiliary patterns are
aligned with a line parallel to the line, and are arranged on the parallel line at the same as a
period of the plural contact hole patterns.

24 (NEW): A mask according to claim 1, wherein centers of the contact hole patterns and a
center of the first auxiliary pattern being at regular periods in a line, the plural second auxiliary
patterns having centers that is offset from the line, and equally distant from both the center of the
first auxiliary pattern and the center of the contact hole pattern that is closest to the second
auxiliary pattern.

25 (NEW): A mask according to claim 1, wherein a distance between centers of the plural
second auxiliary patterns and the line is a period of the plural contact hole patterns.

26 (NEW): A mask designing method according to claim 20, wherein centers of the plural
auxiliary patterns are aligned with a line parallel to the line, and are arranged on the parallel line
at the same as a period of the plural contact hole patterns.

27 (NEW): A mask designing method according to claim 20, wherein centers of the contact
hole patterns and a center of the first auxiliary pattern being at regular periods in a line, the plural
second auxiliary patterns having a center that is offset from the line, and equally distant from
both the center of the first auxiliary pattern and the center of the contact hole pattern that is
closest to the second auxiliary pattern.